

SILICON PLANAR ZENER DIODES

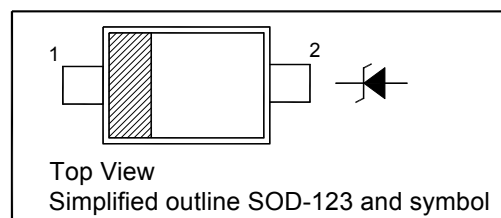
BZT52C...W

Features

- Ideally suited for automated assembly processes
- Total power dissipation: max. 500 mW

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit
Power Dissipation	P _{tot}	500	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 65 to + 150	°C

Characteristics at T_a = 25°C

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient Air	R _{thA}	340	°C/W
Forward Voltage at I _F = 10 mA	V _F	0.9	V

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Characteristics at Ta = 25°C

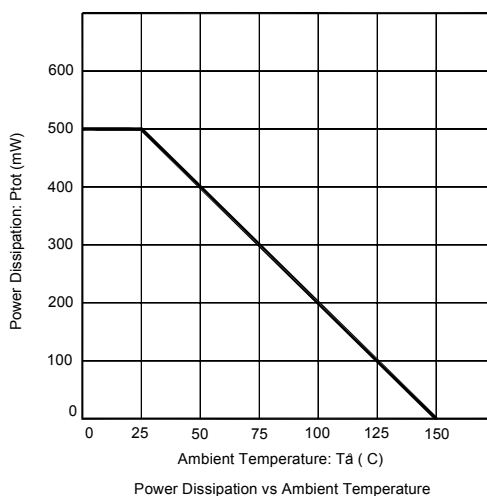
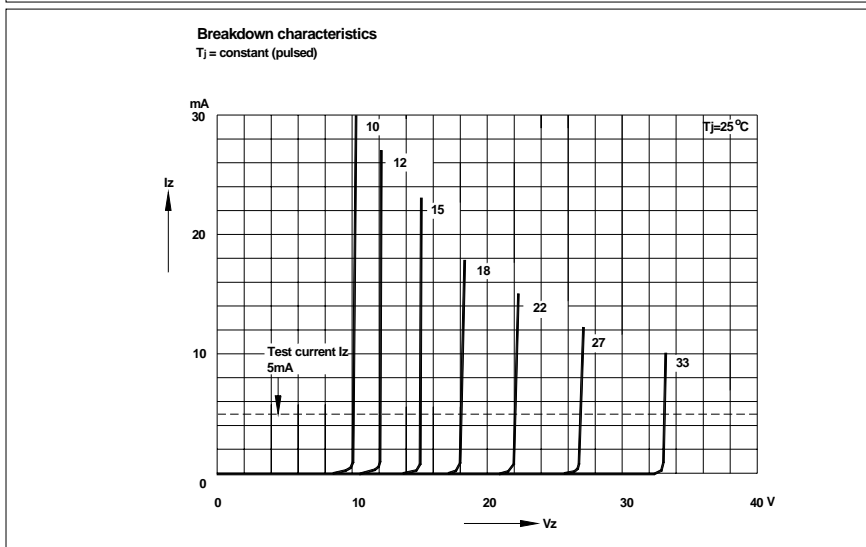
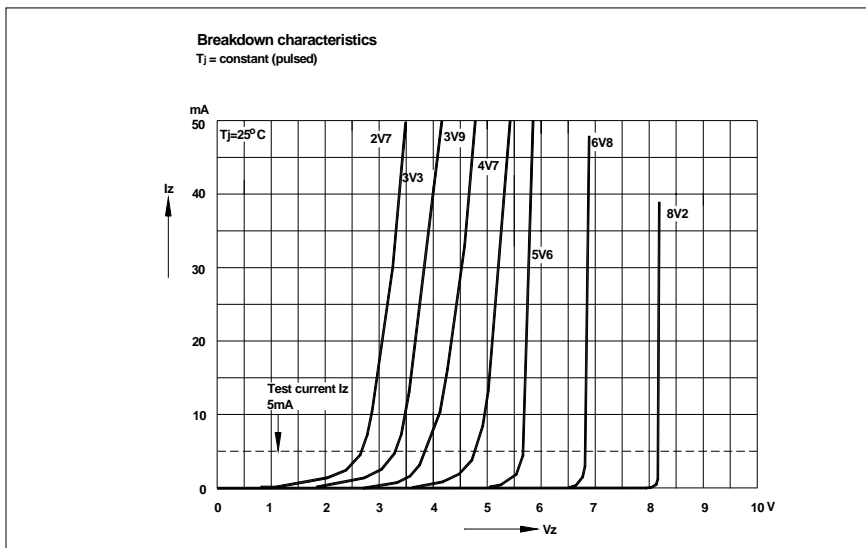
Type	Marking Code	Zener Voltage Range ¹⁾			Dynamic Impedance				Reverse Leakage Current	
		V _{znom}	V _{ZT}	at I _{ZT}	Z _{ZT}	at I _{ZT}	Z _{ZK}	at I _{ZK}	I _R	at V _R
		V	V	mA	Max. (Ω)	mA	Max. (Ω)	mA	Max. (μA)	V
BZT52C2V4W	MH	2.4	2.2...2.6	5	100	5	600	1	50	1
BZT52C2V7W	MJ	2.7	2.5...2.9	5	100	5	600	1	20	1
BZT52C3V0W	MK	3.0	2.8...3.2	5	95	5	600	1	10	1
BZT52C3V3W	MM	3.3	3.1...3.5	5	95	5	600	1	5	1
BZT52C3V6W	MN	3.6	3.4...3.8	5	90	5	600	1	5	1
BZT52C3V9W	MP	3.9	3.7...4.1	5	90	5	600	1	3	1
BZT52C4V3W	MR	4.3	4...4.6	5	90	5	600	1	3	1
BZT52C4V7W	MX	4.7	4.4...5	5	80	5	500	1	3	2
BZT52C5V1W	MY	5.1	4.8...5.4	5	60	5	480	1	2	2
BZT52C5V6W	MZ	5.6	5.2...6	5	40	5	400	1	1	2
BZT52C6V2W	NA	6.2	5.8...6.6	5	10	5	150	1	3	4
BZT52C6V8W	NB	6.8	6.4...7.2	5	15	5	80	1	2	4
BZT52C7V5W	NC	7.5	7...7.9	5	15	5	80	1	1	5
BZT52C8V2W	ND	8.2	7.7...8.7	5	15	5	80	1	0.7	5
BZT52C9V1W	NE	9.1	8.5...9.6	5	15	5	100	1	0.5	6
BZT52C10W	NF	10	9.4...10.6	5	20	5	150	1	0.2	7
BZT52C11W	NH	11	10.4...11.6	5	20	5	150	1	0.1	8
BZT52C12W	NJ	12	11.4...12.7	5	25	5	150	1	0.1	8
BZT52C13W	NK	13	12.4...14.1	5	30	5	170	1	0.1	8
BZT52C15W	NM	15	13.8...15.6	5	30	5	200	1	0.1	10.5
BZT52C16W	NN	16	15.3...17.1	5	40	5	200	1	0.1	11.2
BZT52C18W	NP	18	16.8...19.1	5	45	5	225	1	0.1	12.6
BZT52C20W	NR	20	18.8...21.2	5	55	5	225	1	0.1	14
BZT52C22W	NX	22	20.8...23.3	5	55	5	250	1	0.1	15.4
BZT52C24W	NY	24	22.8...25.6	5	70	5	250	1	0.1	16.8
BZT52C27W	NZ	27	25.1...28.9	2	80	2	300	0.5	0.1	18.9
BZT52C30W	PA	30	28...32	2	80	2	300	0.5	0.1	21
BZT52C33W	PB	33	31...35	2	80	2	325	0.5	0.1	23.1
BZT52C36W	PC	36	34...38	2	90	2	350	0.5	0.1	25.2
BZT52C39W	PD	39	37...41	2	130	2	350	0.5	0.1	27.3
BZT52C43W	6A	43	40...46	2.5	130	2	500	1	2	33
BZT52C47W	6B	47	44...50	2.5	150	2	500	1	2	36
BZT52C51W	6C	51	48...54	2.5	180	2	500	1	1	39
BZT52C56W	6D	56	52...60	2.5	180	2	500	1	1	43
BZT52C62W	6E	62	58...66	2.5	200	2	500	1	0.2	47
BZT52C68W	6F	68	64...72	2.5	250	2	500	1	0.2	52
BZT52C75W	6H	75	70...79	2.5	300	2	500	1	0.2	57

¹⁾ V_{ZT} is tested with pulses (20 ms).



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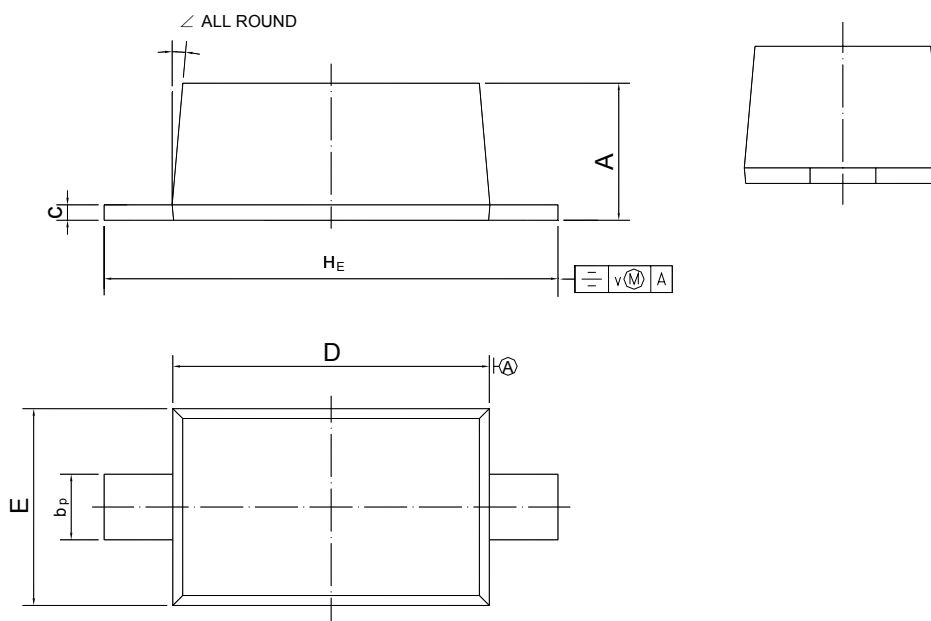


**SILICON PLANAR ZENER DIODES
PACKAGE OUTLINE**

BZT52C...W

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	b _p	c	D	E	H _E	v	∠
mm	1.15 1.05	0.6 0.5	0.135 0.100	2.7 2.6	1.65 1.55	3.85 3.55	0.2	5°